

## **isc Silicon NPN Power Transistors**

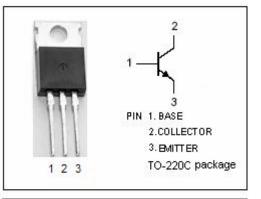
## 2SC3590

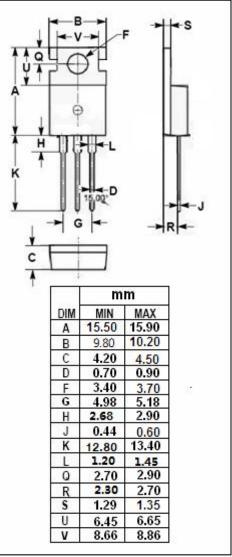
#### DESCRIPTION

- · Collector-Emitter Breakdown Voltage-
- : V<sub>(BR)CEO</sub>= 150V(Min)
- · Fast Switching Speed
- · Low Saturation Voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **APPLICATIONS**

 Designed for high definition CRT display horizontal deflection output applications.





#### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER VALUE		UNIT				
V <sub>CBO</sub>	Collector-Base Voltage	330	V				
V <sub>CEO</sub>	Collector-Emitter Voltage	150	V				
V <sub>EBO</sub>	Emitter-Base Voltage	6	V				
lc	Collector Current-Continuous	7	A				
Ісм	Collector Current-Peak	12	A				
Ι <sub>Β</sub>	Base Current-Continuous	4	A				
Ρτ	Total Power Dissipation @ T <sub>C</sub> =25℃	50	W				
TJ	Junction Temperature	150	°C				
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C				



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# 2SC3590

#### **ELECTRICAL CHARACTERISTICS**

#### $T_{\text{C}}\text{=}25\,^{\circ}\!\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>E</sub> = 0	330			V
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	$I_{C}$ = 1mA; $R_{BE}$ = $\infty$	150			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1m A; I <sub>C</sub> = 0	6			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 0.5A			0.8	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 0.5A			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 180V; I <sub>E</sub> = 0			100	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			100	μA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 1V	15			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 5A; V <sub>CE</sub> = 1V	10		50	
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 10V		40		MHz
tr	Fall Time	I <sub>C</sub> = 5A, I <sub>B1</sub> = -I <sub>B2</sub> = 0.5A			0.3	μs

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